2SA1309A

Silicon PNP epitaxial planar type

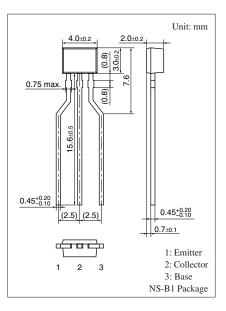
For low-frequency amplification Complementary to 2SC3311A

Features

- \bullet High forward current transfer ratio $h_{F\!E}$
- Allowing supply with the radial taping
- Optimum for high-density mounting

Parameter	Symbol	Rating	Unit				
Collector-base voltage (Emitter open)	V _{CBO}	-60	V				
Collector-emitter voltage (Base open)	V _{CEO}	-50	V				
Emitter-base voltage (Collector open)	V _{EBO}	-7	V				
Collector current	I _C	-100	mA				
Peak collector current	I _{CP}	-200	mA				
Collector power dissipation	P _C	300	mW				
Junction temperature	Tj	150	°C				
Storage temperature	T _{stg}	-55 to +150	°C				

Absolute Maximum Ratings $T_a = 25^{\circ}C$

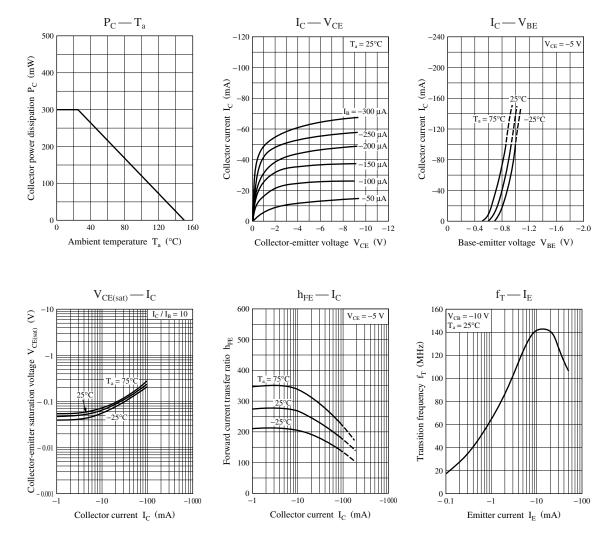


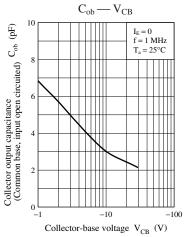
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions		Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu A, \ I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = -10 \ \mu A, \ I_{\rm C} = 0$	-7			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -10 \text{ V}, I_E = 0$			-100	nA
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -10 \text{ V}, I_B = 0$			-1	μΑ
Forward current transfer ratio *	h _{FE}	$V_{CE} = -10 \text{ V}, I_C = -2 \text{ mA}$	160		460	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -50$ mA, $I_{\rm B} = -5$ mA			- 0.3	V
Transition frequency	f _T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		3.5		pF
(Common base, input open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Rank classification

Rank	Q	R	S	No rank
h _{FE}	160 to 260	210 to 340	290 to 460	160 to 460





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